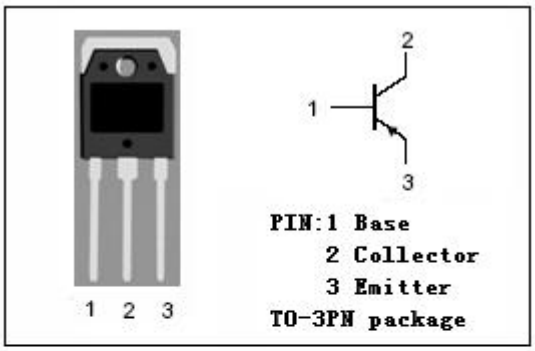
isc Silicon PNP Power Transistor — 2SB757

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -40V(Min)
- Good Linearity of h_{FE}
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD847
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

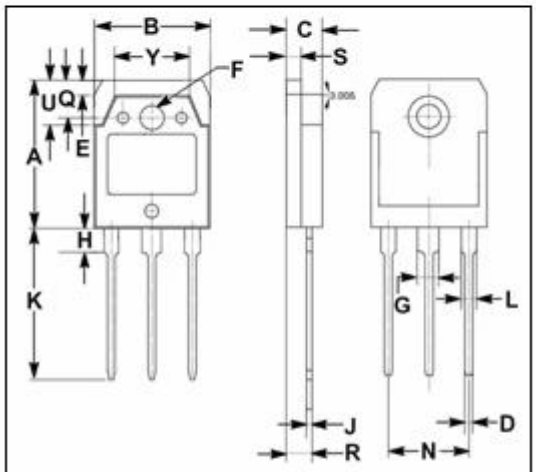
- Audio amplifier applications
- Series regulators
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current- Continuous	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.56	℃/W



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.1mA; I_E= 0	-40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -0.1mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5.0A; I_B= -0.5A			-0.8	V
$V_{BE(sat)}$	Base -Emitter Saturation Voltage	I_C= -5.0A; I_B= -0.5A			-1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E=0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-10	μA
h_{FE}	DC Current Gain	I_C= -5A; V_{CE}= -2V	40		240	